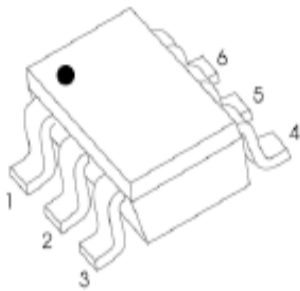
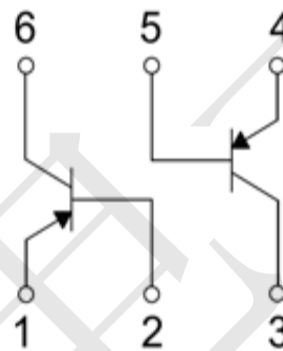


FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors



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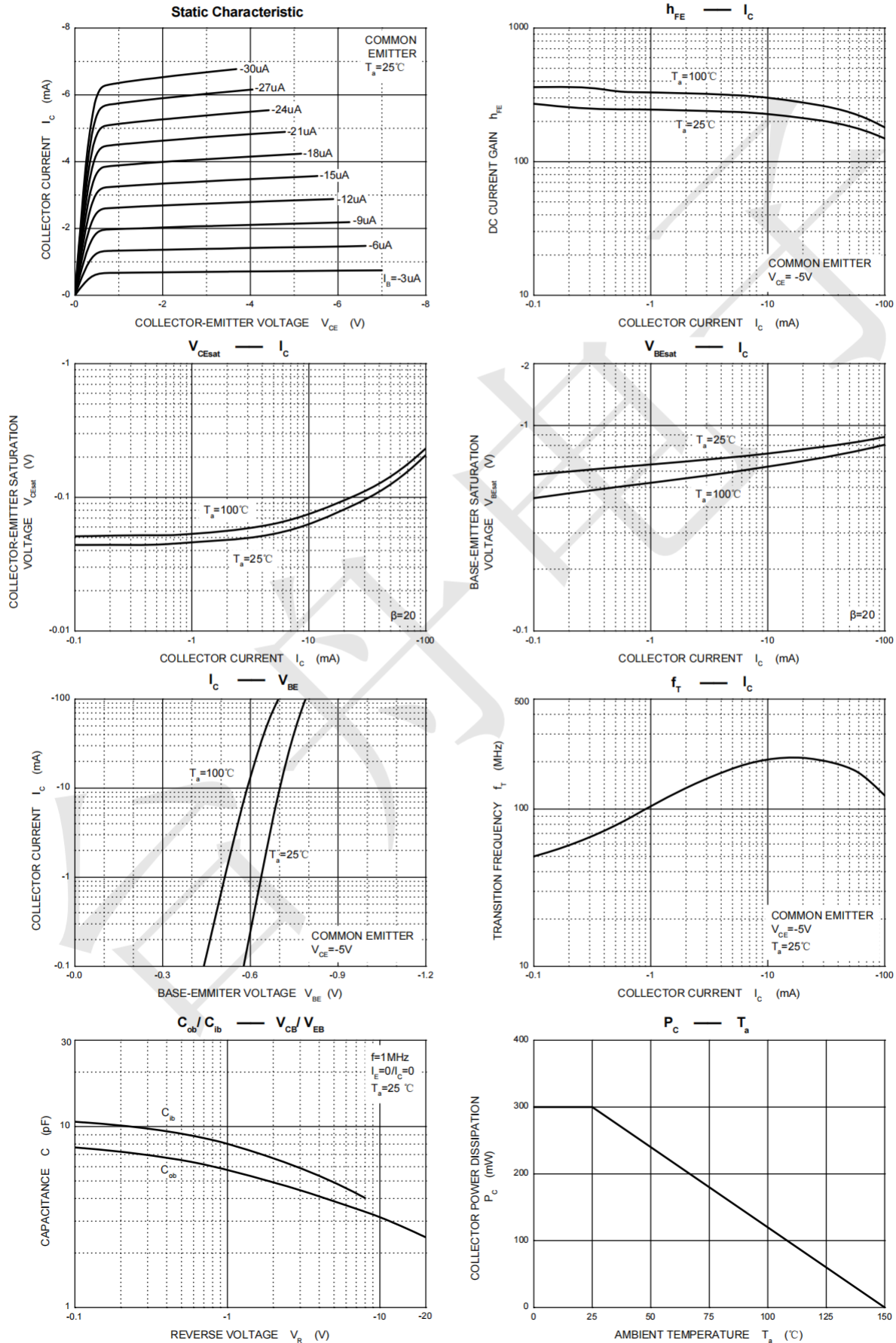
MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector- Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.2	A
P_C	Collector Power Dissipation	0.3	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	417	$^{\circ}\text{C}/\text{W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

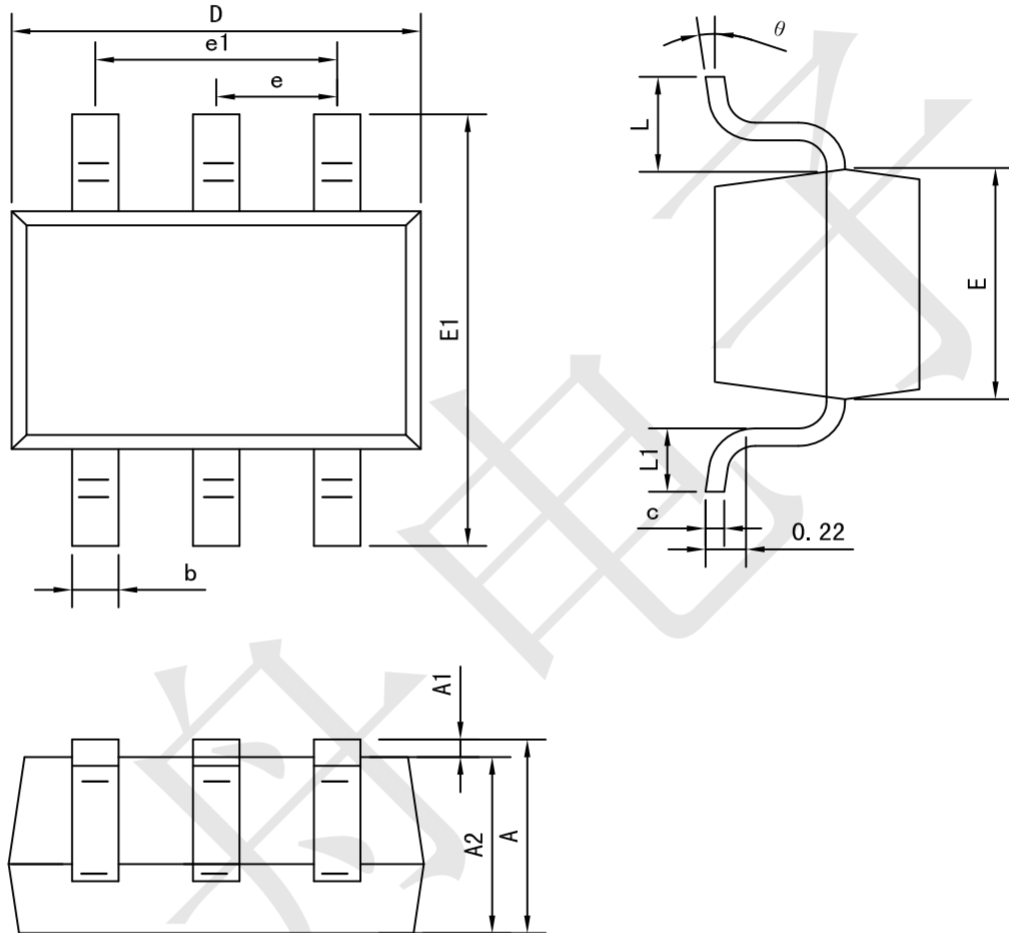
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-15	nA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -2mA$	240		420	
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$	$I_C = -10mA, I_B = -0.5mA$			-0.3	V
	$V_{CE(sat)(2)}$	$I_C = -100mA, I_B = -5mA$			-0.65	V
Base-emitter voltage	$V_{BE(1)}$	$V_{CE} = -5V, I_C = -2mA$	-0.6		-0.75	V
	$V_{BE(2)}$	$V_{CE} = -5V, I_C = -10mA$			-0.82	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		3.5		pF
Noise figure	NF	$V_{CE} = -5V, I_C = -0.2mA,$ $f = 1kHz, R_s = 2K\Omega, BW = 200Hz$		2.5		dB

Typical Characteristics



Package outline dimensions

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Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°